

# ANTREX Electronics

Electronic Components Sourcing Information

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## Product Reference Information

**Part Number:** FZ1800R17KF4NOSA1  
**Manufacturer:** Infineon Technologies  
**Package:** Module  
**Availability:** Please confirm with sales

**Product Page:**

<https://antrexco.com/product/details/infineon-technologies/fz1800r17kf4nosa1.html>

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## Contact Information

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## Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

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**Note:**

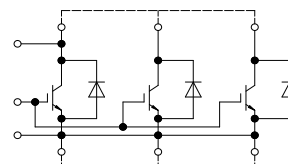
This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

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IHM-B Modul mit Trench/Feldstopp IGBT4 und Emitter Controlled 4 Diode  
IHM-B module with Trench/Fieldstop IGBT4 and Emitter Controlled 4 diode

### Vorläufige Daten / Preliminary Data



external connection  
(to be done)

$V_{CES} = 1200V$

$I_{C\ nom} = 2400A / I_{CRM} = 4800A$

### Typische Anwendungen

- Hochleistungsumrichter
- Motorantriebe

### Elektrische Eigenschaften

- Erweiterte Sperrschichttemperatur  $T_{vj\ op}$
- Niedrige Schaltverluste

### Mechanische Eigenschaften

- Gehäuse mit CTI > 400
- Hohe Leistungsdichte
- IHM B Gehäuse

### Typical Applications

- High power converters
- Motor drives

### Electrical Features

- Extended operating temperature  $T_{vj\ op}$
- Low switching losses

### Mechanical Features

- Package with CTI > 400
- High power density
- IHM B housing

### Module Label Code

#### Barcode Code 128



#### DMX - Code



#### Content of the Code

|                            | Digit   |
|----------------------------|---------|
| Module Serial Number       | 1 - 5   |
| Module Material Number     | 6 - 11  |
| Production Order Number    | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

|                 |                                 |                      |
|-----------------|---------------------------------|----------------------|
| prepared by: WB | date of publication: 2015-09-29 |                      |
| approved by: IB | revision: V2.4                  | UL approved (E83335) |

Vorläufige Daten  
Preliminary Data

## IGBT, Wechselrichter / IGBT, Inverter

## Höchstzulässige Werte / Maximum Rated Values

|                                                                          |                                                                                                                               |                            |              |        |
|--------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------|----------------------------|--------------|--------|
| Kollektor-Emitter-Sperrspannung<br>Collector-emitter voltage             | $T_{vj} = 25^{\circ}\text{C}$                                                                                                 | $V_{CES}$                  | 1200         | V      |
| Kollektor-Dauergleichstrom<br>Continuous DC collector current            | $T_C = 100^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$<br>$T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$ | $I_{C\text{nom}}$<br>$I_C$ | 2400<br>3560 | A<br>A |
| Periodischer Kollektor-Spitzenstrom<br>Repetitive peak collector current | $t_P = 1\text{ ms}$                                                                                                           | $I_{CRM}$                  | 4800         | A      |
| Gesamt-Verlustleistung<br>Total power dissipation                        | $T_C = 25^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$                                                                  | $P_{\text{tot}}$           | 13,5         | kW     |
| Gate-Emitter-Spitzenspannung<br>Gate-emitter peak voltage                |                                                                                                                               | $V_{GES}$                  | +/-20        | V      |

## Charakteristische Werte / Characteristic Values

|                                                                                 |                                                                                                                                                                                               |                                                                                                   | min.               | typ.                 | max. |                                                 |
|---------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|--------------------|----------------------|------|-------------------------------------------------|
| Kollektor-Emitter-Sättigungsspannung<br>Collector-emitter saturation voltage    | $I_C = 2400\text{ A}, V_{GE} = 15\text{ V}$<br>$I_C = 2400\text{ A}, V_{GE} = 15\text{ V}$<br>$I_C = 2400\text{ A}, V_{GE} = 15\text{ V}$                                                     | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{sat}}$ | 1,75<br>2,00<br>2,05 | 2,10 | V<br>V<br>V                                     |
| Gate-Schwellenspannung<br>Gate threshold voltage                                | $I_C = 91,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                          |                                                                                                   | $V_{GEth}$         | 5,20                 | 5,80 | 6,40 V                                          |
| Gateladung<br>Gate charge                                                       | $V_{GE} = -15\text{ V} \dots +15\text{ V}$                                                                                                                                                    |                                                                                                   | $Q_G$              | 18,5                 |      | $\mu\text{C}$                                   |
| Interner Gatewiderstand<br>Internal gate resistor                               | $T_{vj} = 25^{\circ}\text{C}$                                                                                                                                                                 |                                                                                                   | $R_{Gint}$         | 0,98                 |      | $\Omega$                                        |
| Eingangskapazität<br>Input capacitance                                          | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$                                                                                                    |                                                                                                   | $C_{ies}$          | 150                  |      | nF                                              |
| Rückwirkungskapazität<br>Reverse transfer capacitance                           | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$                                                                                                    |                                                                                                   | $C_{res}$          | 8,30                 |      | nF                                              |
| Kollektor-Emitter-Reststrom<br>Collector-emitter cut-off current                | $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                    |                                                                                                   | $I_{CES}$          |                      | 5,0  | mA                                              |
| Gate-Emitter-Reststrom<br>Gate-emitter leakage current                          | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$                                                                                                                      |                                                                                                   | $I_{GES}$          |                      | 400  | nA                                              |
| Einschaltverzögerungszeit, induktive Last<br>Turn-on delay time, inductive load | $I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Gon} = 1,5\ \Omega$                                                                                         | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_{don}$          | 0,50<br>0,54<br>0,55 |      | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| Anstiegszeit, induktive Last<br>Rise time, inductive load                       | $I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Gon} = 1,5\ \Omega$                                                                                         | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_r$              | 0,33<br>0,33<br>0,33 |      | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| Abschaltverzögerungszeit, induktive Last<br>Turn-off delay time, inductive load | $I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Goff} = 0,22\ \Omega$                                                                                       | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_{doff}$         | 1,00<br>1,15<br>1,15 |      | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| Fallzeit, induktive Last<br>Fall time, inductive load                           | $I_C = 2400\text{ A}, V_{CE} = 600\text{ V}$<br>$V_{GE} = \pm 15\text{ V}$<br>$R_{Goff} = 0,22\ \Omega$                                                                                       | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $t_f$              | 0,24<br>0,16<br>0,17 |      | $\mu\text{s}$<br>$\mu\text{s}$<br>$\mu\text{s}$ |
| Einschaltverlustenergie pro Puls<br>Turn-on energy loss per pulse               | $I_C = 2400\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$<br>$V_{GE} = \pm 15\text{ V}, di/dt = 6250\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$<br>$R_{Gon} = 1,5\ \Omega$   | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $E_{on}$           | 365<br>460<br>505    |      | mJ<br>mJ<br>mJ                                  |
| Abschaltverlustenergie pro Puls<br>Turn-off energy loss per pulse               | $I_C = 2400\text{ A}, V_{CE} = 600\text{ V}, L_S = 50\text{ nH}$<br>$V_{GE} = \pm 15\text{ V}, du/dt = 2750\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$<br>$R_{Goff} = 0,22\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $E_{off}$          | 430<br>455<br>480    |      | mJ<br>mJ<br>mJ                                  |
| Kurzschlußverhalten<br>SC data                                                  | $V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$<br>$V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$<br>$t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$                                   |                                                                                                   | $I_{SC}$           | 9600                 |      | A                                               |
| Wärmewiderstand, Chip bis Gehäuse<br>Thermal resistance, junction to case       | pro IGBT / per IGBT                                                                                                                                                                           |                                                                                                   | $R_{thJC}$         |                      | 11,0 | K/kW                                            |
| Wärmewiderstand, Gehäuse bis Kühlkörper<br>Thermal resistance, case to heatsink | pro IGBT / per IGBT<br>$\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$                                           |                                                                                                   | $R_{thCH}$         | 6,50                 |      | K/kW                                            |
| Temperatur im Schaltbetrieb<br>Temperature under switching conditions           |                                                                                                                                                                                               |                                                                                                   | $T_{vj\text{op}}$  | -40                  | 150  | $^{\circ}\text{C}$                              |

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Vorläufige Daten  
Preliminary Data

## Diode, Wechselrichter / Diode, Inverter

## Höchstzulässige Werte / Maximum Rated Values

|                                                                     |                                                                                                                                              |           |            |                                                |
|---------------------------------------------------------------------|----------------------------------------------------------------------------------------------------------------------------------------------|-----------|------------|------------------------------------------------|
| Periodische Spitzensperrspannung<br>Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$                                                                                                                | $V_{RRM}$ | 1200       | V                                              |
| Dauergleichstrom<br>Continuous DC forward current                   |                                                                                                                                              | $I_F$     | 2400       | A                                              |
| Periodischer Spitzenstrom<br>Repetitive peak forward current        | $t_P = 1\text{ ms}$                                                                                                                          | $I_{FRM}$ | 4800       | A                                              |
| Grenzlastintegral<br>$I^2t$ - value                                 | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$<br>$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | $I^2t$    | 750<br>725 | $\text{kA}^2\text{s}$<br>$\text{kA}^2\text{s}$ |

## Charakteristische Werte / Characteristic Values

|                                                                                 |                                                                                                                                             |                                                                                                   | min.               | typ. | max.                 |                                                 |
|---------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|--------------------|------|----------------------|-------------------------------------------------|
| Durchlassspannung<br>Forward voltage                                            | $I_F = 2400\text{ A}, V_{GE} = 0\text{ V}$<br>$I_F = 2400\text{ A}, V_{GE} = 0\text{ V}$<br>$I_F = 2400\text{ A}, V_{GE} = 0\text{ V}$      | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $V_F$              |      | 1,80<br>1,75<br>1,70 | V<br>V<br>V                                     |
| Rückstromspitze<br>Peak reverse recovery current                                | $I_F = 2400\text{ A}, -di_F/dt = 6250\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$<br>$V_R = 600\text{ V}$<br>$V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $I_{RM}$           |      | 805<br>1150<br>1200  | A<br>A<br>A                                     |
| Sperrverzögerungsladung<br>Recovered charge                                     | $I_F = 2400\text{ A}, -di_F/dt = 6250\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$<br>$V_R = 600\text{ V}$<br>$V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $Q_r$              |      | 245<br>430<br>490    | $\mu\text{C}$<br>$\mu\text{C}$<br>$\mu\text{C}$ |
| Abschaltenergie pro Puls<br>Reverse recovery energy                             | $I_F = 2400\text{ A}, -di_F/dt = 6250\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$<br>$V_R = 600\text{ V}$<br>$V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$<br>$T_{vj} = 125^{\circ}\text{C}$<br>$T_{vj} = 150^{\circ}\text{C}$ | $E_{rec}$          |      | 105<br>185<br>210    | mJ<br>mJ<br>mJ                                  |
| Wärmewiderstand, Chip bis Gehäuse<br>Thermal resistance, junction to case       | pro Diode / per diode                                                                                                                       |                                                                                                   | $R_{thJC}$         |      |                      | 17,5 K/kW                                       |
| Wärmewiderstand, Gehäuse bis Kühlkörper<br>Thermal resistance, case to heatsink | pro Diode / per diode<br>$\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$   |                                                                                                   | $R_{thCH}$         |      | 7,20                 | K/kW                                            |
| Temperatur im Schaltbetrieb<br>Temperature under switching conditions           |                                                                                                                                             |                                                                                                   | $T_{vj\text{ op}}$ | -40  |                      | 150 $^{\circ}\text{C}$                          |

**Vorläufige Daten**  
**Preliminary Data**
**Modul / Module**

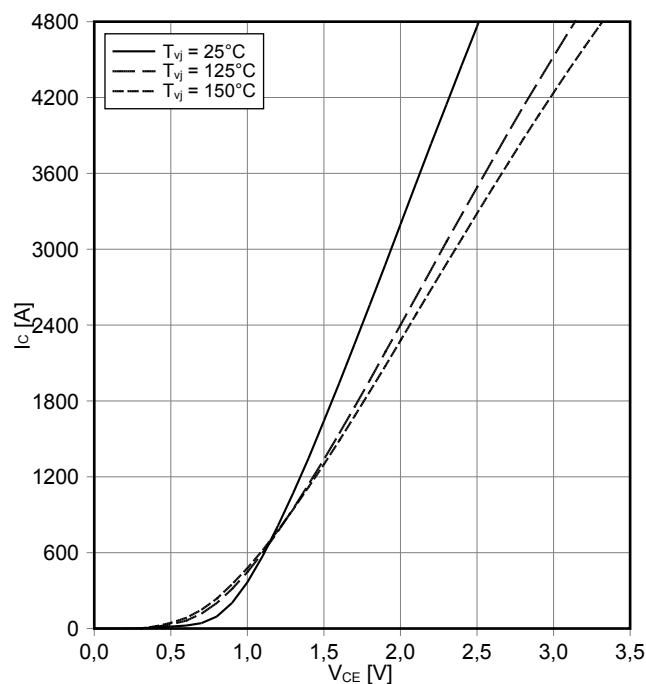
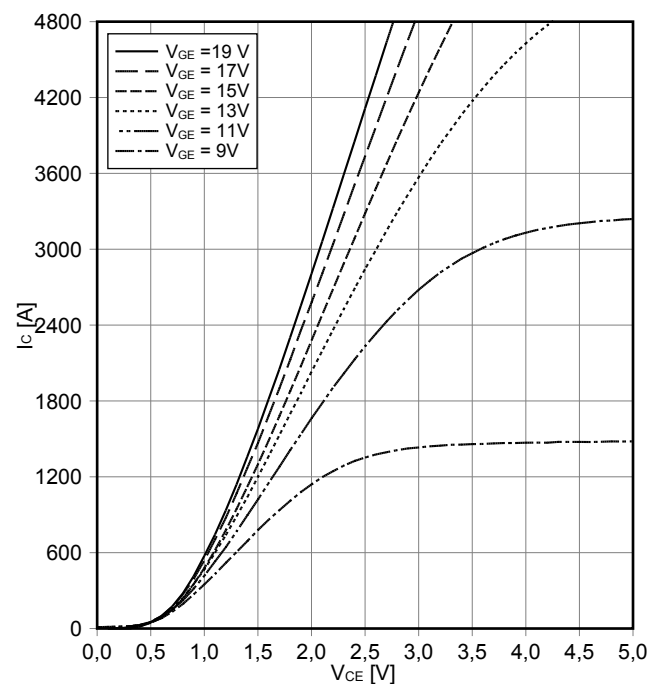
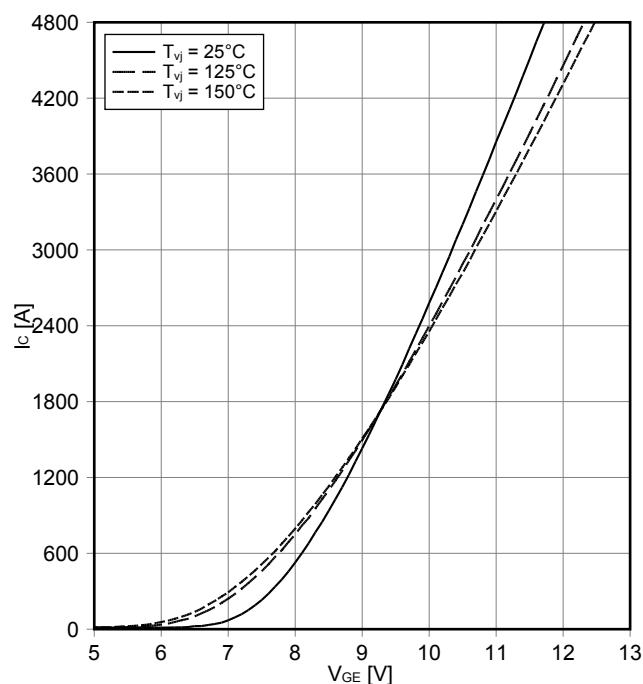
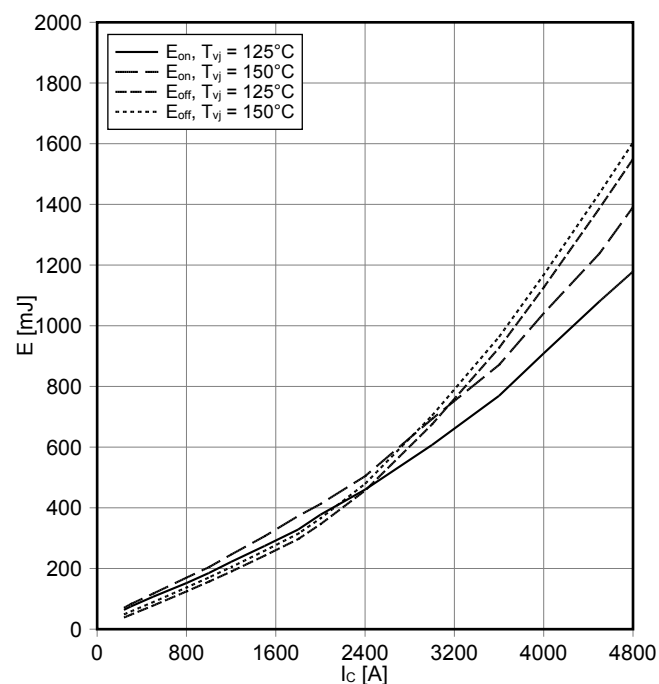
|                                                                                        |                                                                                                                    |                      |                                |      |         |
|----------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------|----------------------|--------------------------------|------|---------|
| Isolations-Prüfspannung<br>Isolation test voltage                                      | RMS, f = 50 Hz, t = 1 min.                                                                                         | V <sub>ISOL</sub>    | 2,5                            |      | kV      |
| Material Modulgrundplatte<br>Material of module baseplate                              |                                                                                                                    |                      | Cu                             |      |         |
| Innere Isolation<br>Internal isolation                                                 | Basisisolation (Schutzklasse 1, EN61140)<br>basic insulation (class 1, IEC 61140)                                  |                      | Al <sub>2</sub> O <sub>3</sub> |      |         |
| Kriechstrecke<br>Creepage distance                                                     | Kontakt - Kühlkörper / terminal to heatsink<br>Kontakt - Kontakt / terminal to terminal                            |                      | 32,0<br>32,0                   |      | mm      |
| Luftstrecke<br>Clearance                                                               | Kontakt - Kühlkörper / terminal to heatsink<br>Kontakt - Kontakt / terminal to terminal                            |                      | 19,0<br>19,0                   |      | mm      |
| Vergleichszahl der Kriechwegbildung<br>Comperative tracking index                      |                                                                                                                    | CTI                  | > 400                          |      |         |
|                                                                                        |                                                                                                                    |                      |                                |      |         |
|                                                                                        |                                                                                                                    |                      | min.                           | typ. | max.    |
| Modulstreuinduktivität<br>Stray inductance module                                      |                                                                                                                    | L <sub>sCE</sub>     |                                | 6,0  | nH      |
| Modulleitungswiderstand, Anschlüsse - Chip<br>Module lead resistance, terminals - chip | T <sub>C</sub> = 25°C, pro Schalter / per switch                                                                   | R <sub>CC'+EE'</sub> |                                | 0,10 | mΩ      |
| Lagertemperatur<br>Storage temperature                                                 |                                                                                                                    | T <sub>stg</sub>     | -40                            |      | 150 °C  |
| Anzugsdrehmoment f. Modulmontage<br>Mounting torque for modul mounting                 | Schraube M6 - Montage gem. gültiger Applikationsschrift<br>Screw M6 - Mounting according to valid application note | M                    | 4,25                           |      | 5,75 Nm |
| Anzugsdrehmoment f. elektr. Anschlüsse<br>Terminal connection torque                   | Schraube M4 - Montage gem. gültiger Applikationsschrift<br>Screw M4 - Mounting according to valid application note | M                    | 1,7                            | -    | 2,1 Nm  |
|                                                                                        | Schraube M8 - Montage gem. gültiger Applikationsschrift<br>Screw M8 - Mounting according to valid application note |                      | 8,0                            | -    | 10 Nm   |
| Gewicht<br>Weight                                                                      |                                                                                                                    | G                    |                                | 1900 | g       |

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Vorläufige Daten  
Preliminary DataAusgangskennlinie IGBT, Wechselrichter (typisch)  
output characteristic IGBT, Inverter (typical)
 $I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$ 
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)  
output characteristic IGBT, Inverter (typical)
 $I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$ 
Übertragungscharakteristik IGBT, Wechselrichter (typisch)  
transfer characteristic IGBT, Inverter (typical)
 $I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$ 
Schaltverluste IGBT, Wechselrichter (typisch)  
switching losses IGBT, Inverter (typical)
 $E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 1.5\ \Omega$ ,  $R_{Goff} = 0.22\ \Omega$ ,  $V_{CE} = 600\text{ V}$ 


prepared by: WB

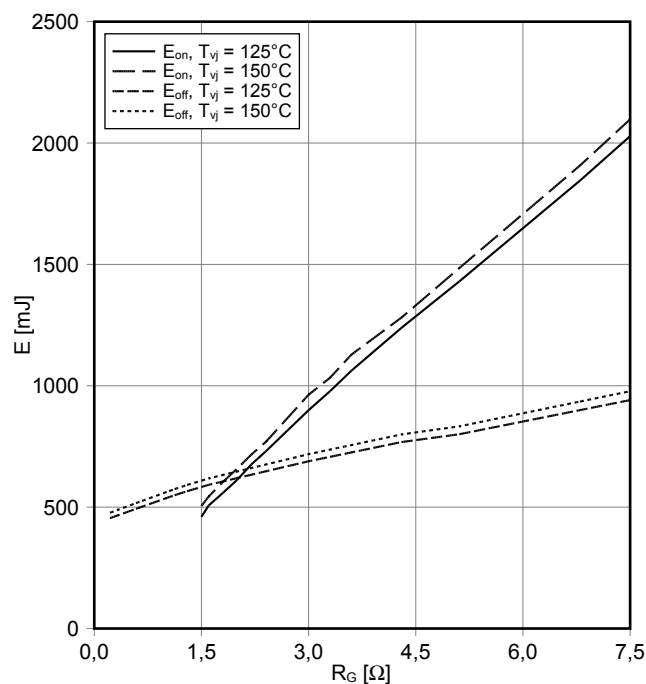
date of publication: 2015-09-29

approved by: IB

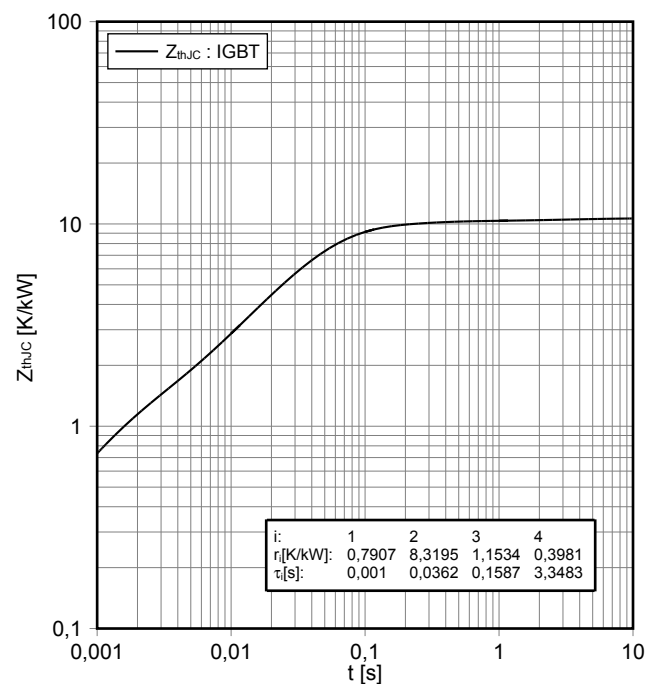
revision: V2.4

# Vorläufige Daten Preliminary Data

## Schaltverluste IGBT, Wechselrichter (typisch) switching losses IGBT, Inverter (typical)

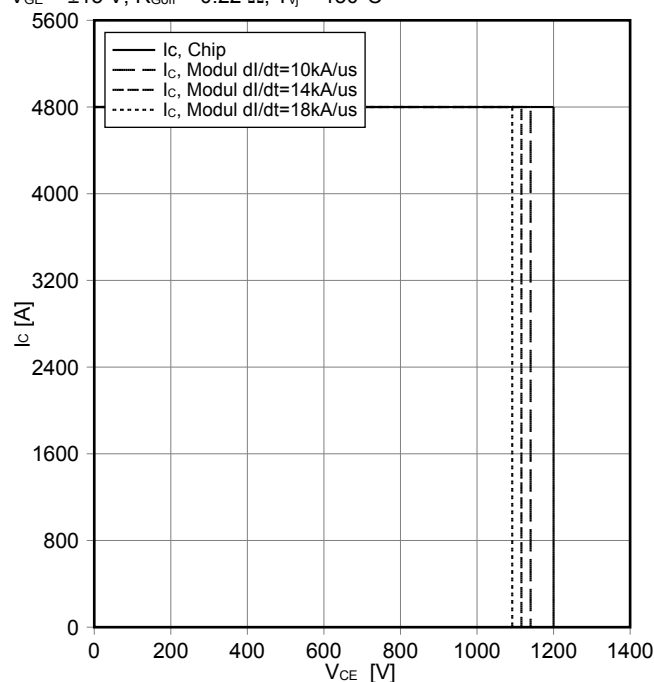
 $E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15 \text{ V}$ ,  $I_C = 2400 \text{ A}$ ,  $V_{CE} = 600 \text{ V}$ 


## Transienter Wärmewiderstand IGBT, Wechselrichter transient thermal impedance IGBT, Inverter

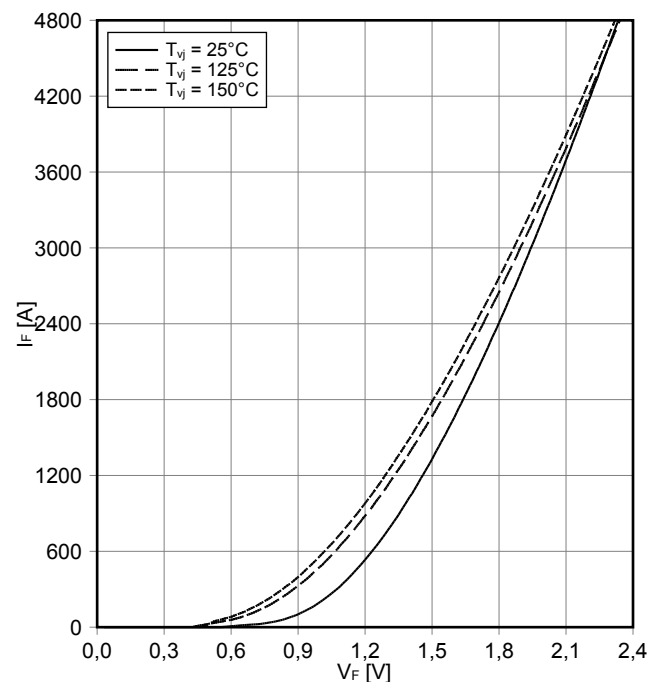
 $Z_{thJC} = f(t)$ 


## Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter (RBSOA)

### reverse bias safe operating area IGBT, Inverter (RBSOA)

 $I_C = f(V_{CE}) = f(dI/dt_{max}, L_S + L_{SCE})$  ( $V_{CE} = 1200 \text{ V} - L_{SCE} \cdot dI/dt_{max}$ )  
 $V_{GE} = \pm 15 \text{ V}$ ,  $R_{Goff} = 0.22 \Omega$ ,  $T_{vj} = 150^\circ\text{C}$ 


## Durchlasskennlinie der Diode, Wechselrichter (typisch) forward characteristic of Diode, Inverter (typical)

 $I_F = f(V_F)$ 


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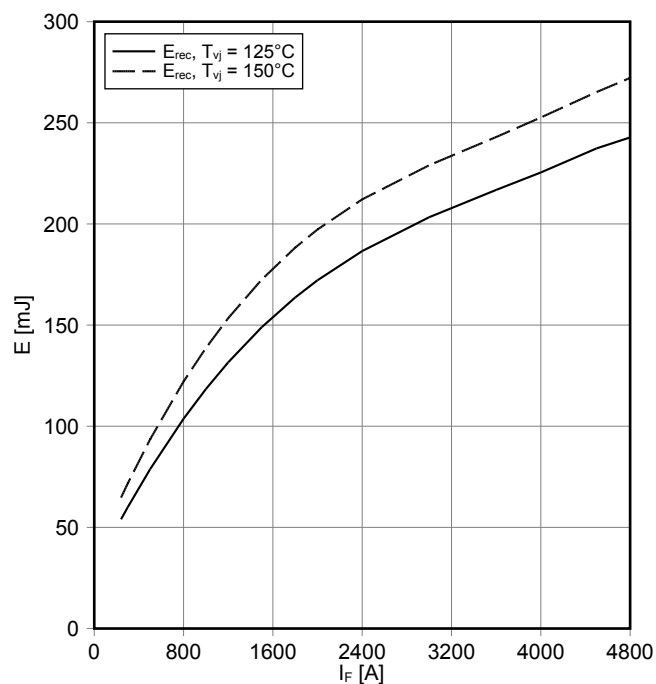
approved by: IB

revision: V2.4

Vorläufige Daten  
Preliminary DataSchaltverluste Diode, Wechselrichter (typisch)  
switching losses Diode, Inverter (typical)

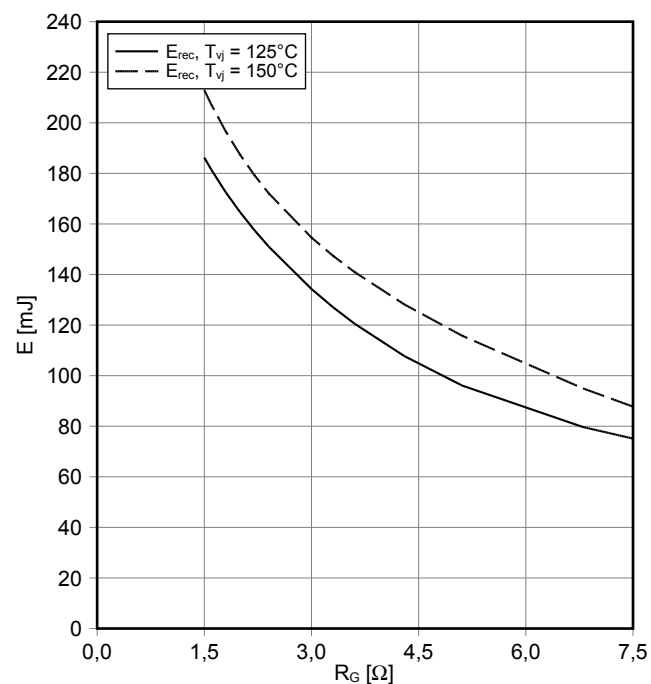
$E_{\text{rec}} = f(I_F)$

$R_{\text{Gon}} = 1.5 \, \Omega, V_{\text{CE}} = 600 \, \text{V}$

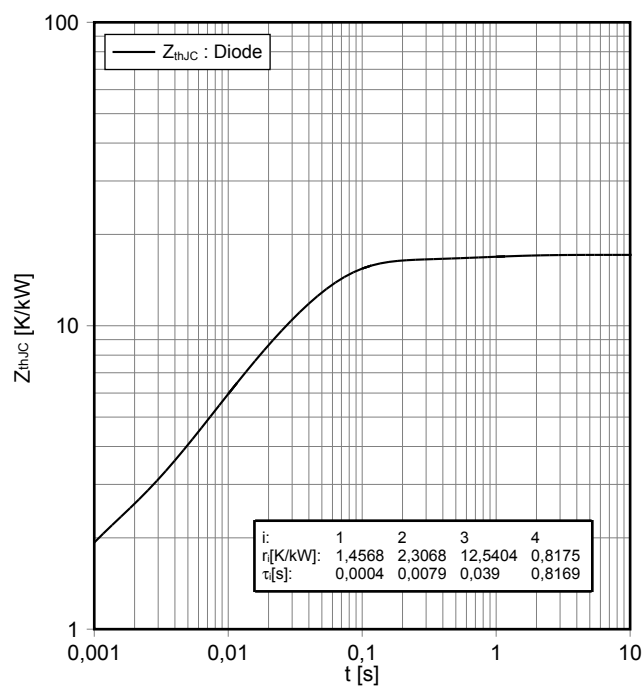
Schaltverluste Diode, Wechselrichter (typisch)  
switching losses Diode, Inverter (typical)

$E_{\text{rec}} = f(R_G)$

$I_F = 2400 \, \text{A}, V_{\text{CE}} = 600 \, \text{V}$

Transienter Wärmewiderstand Diode, Wechselrichter  
transient thermal impedance Diode, Inverter

$Z_{\text{thJC}} = f(t)$



|             |        |        |         |        |
|-------------|--------|--------|---------|--------|
| i:          | 1      | 2      | 3       | 4      |
| $r$ [K/kW]: | 1,4568 | 2,3068 | 12,5404 | 0,8175 |
| $\tau$ [s]: | 0,0004 | 0,0079 | 0,039   | 0,8169 |

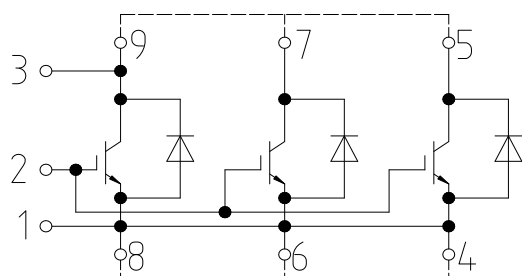
prepared by: WB

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revision: V2.4

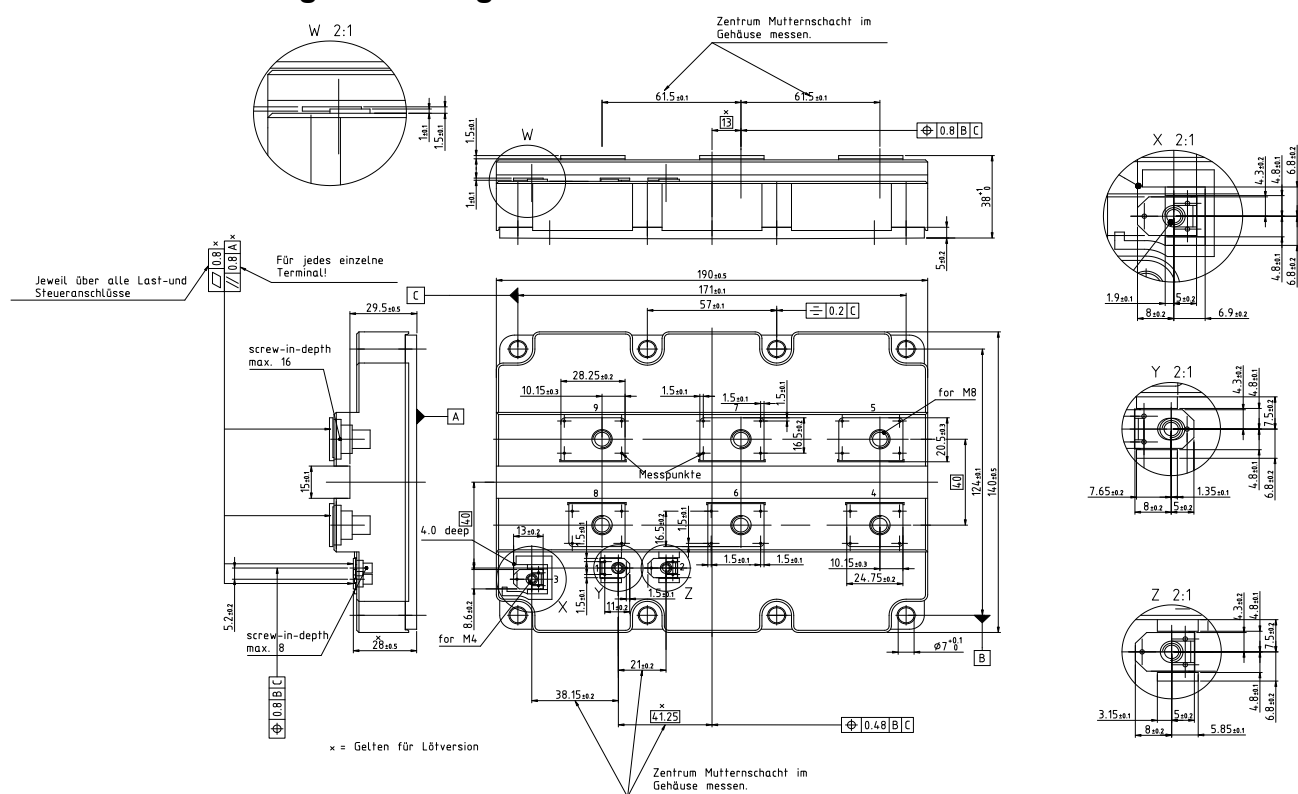
### Schaltplan / Circuit diagram



```
external connection
(to be done)
```

## Vorläufige Daten Preliminary Data

## Gehäuseabmessungen / Package outlines



|                 |                                 |
|-----------------|---------------------------------|
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## Vorläufige Daten Preliminary Data

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